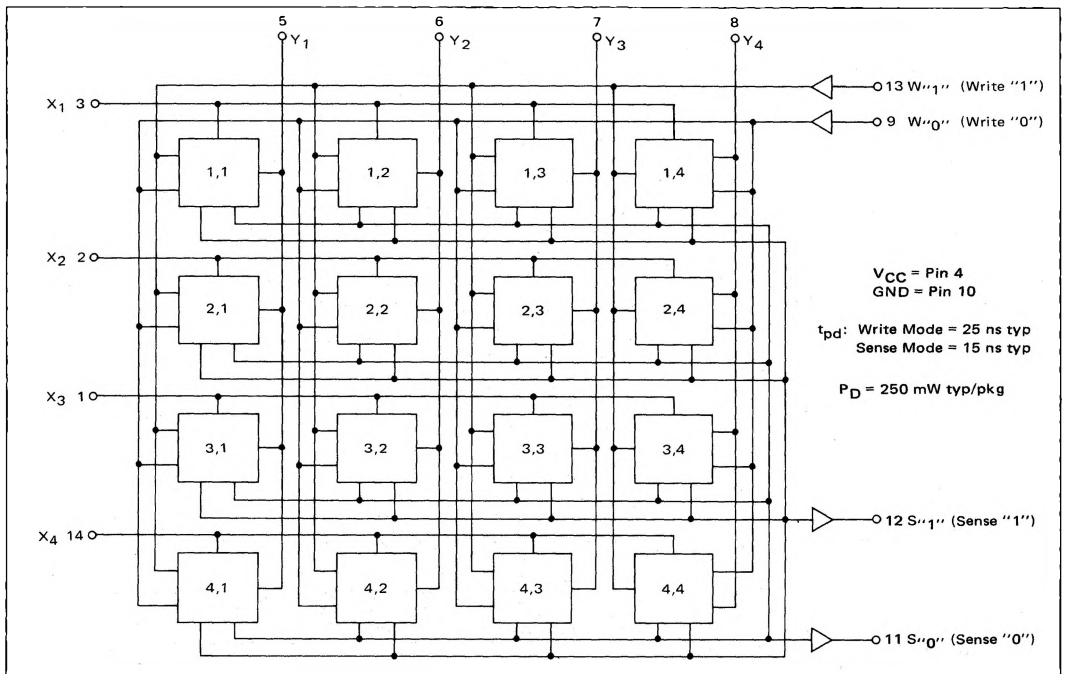


MC4304F,L • MC4305F,L* MC4004F,L,P • MC4005F,L,P*

This 16-Bit memory cell serves as the basic building block for scratch pad memory systems having cycle times of less than 100 ns. The basic cell provides 16 words of one-bit memory operating in the non-destructive readout (NDRO) mode.

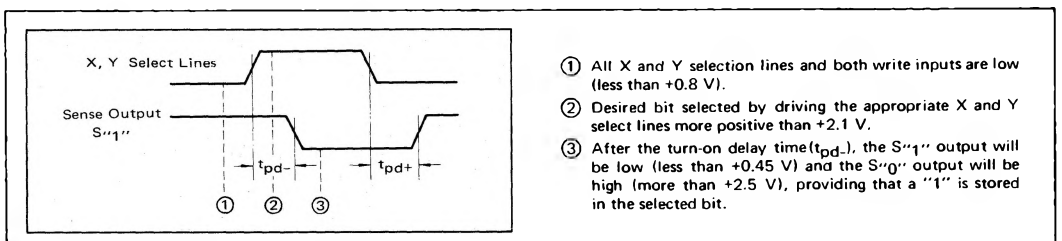
The memory contains 16 flip-flops arranged in a four-by-four matrix. A single bit of the matrix is selected by

driving one of four X select lines and one of four Y select lines above the select threshold. Two sense amplifiers are shared by all 16 bits and provide a double rail output from the selected bit. The sense output of many devices can be "wired ORed" together since the output stage does not have a pullup resistor or network. Two write amplifiers allow a "1" or a "0" to be written into a selected bit.



— OPERATING SEQUENCE —

FIGURE 1 — READ MODE TIMING DIAGRAM

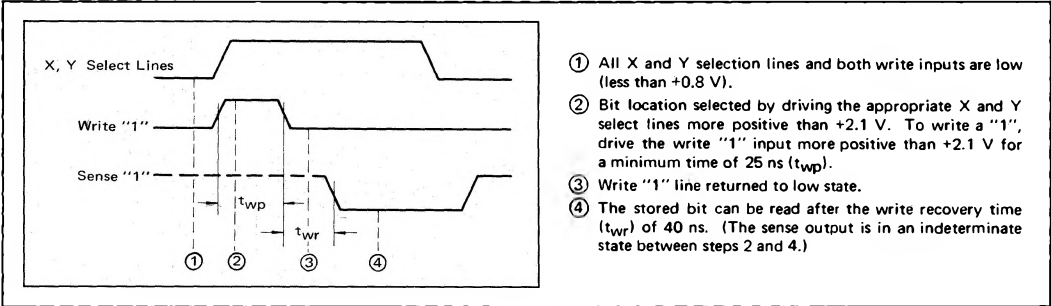


*F suffix = TO-86 ceramic flat package (Case 607).

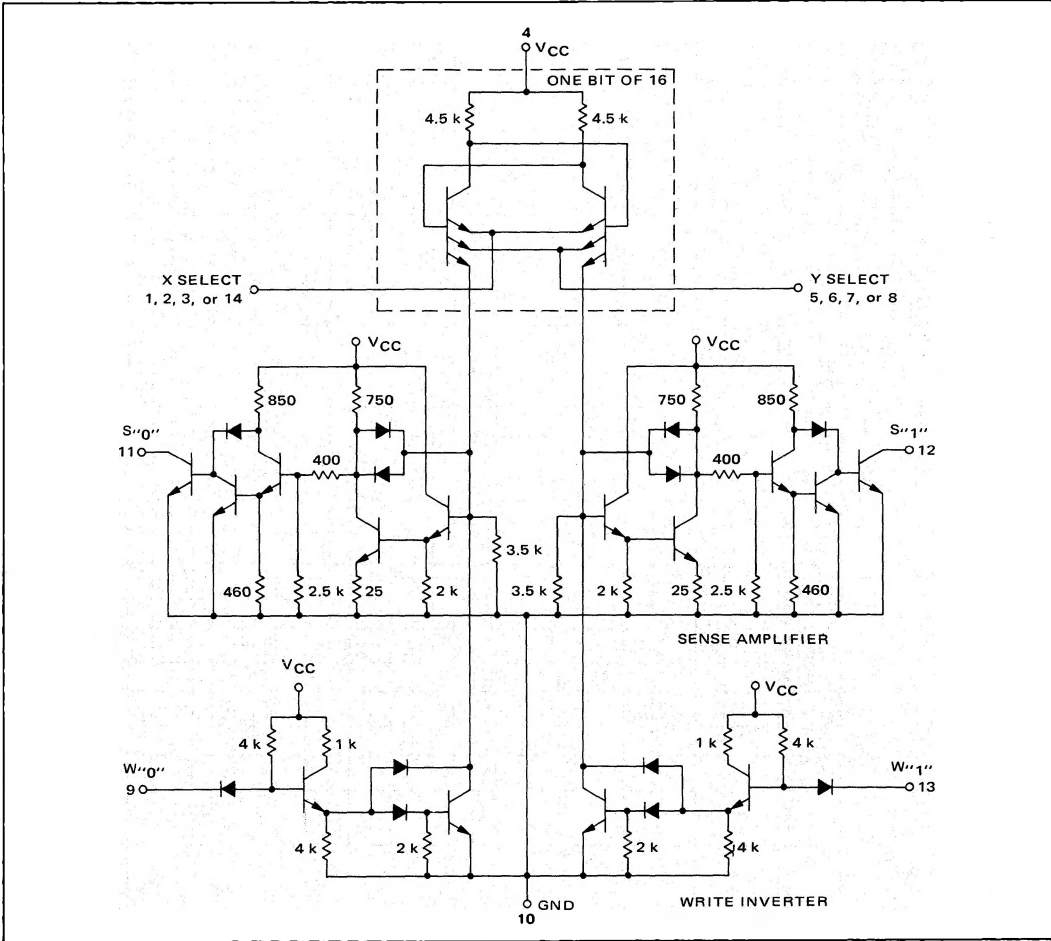
L suffix = TO-116 ceramic dual in-line package (Case 632).

P suffix = TO-116 plastic dual in-line package (Case 605).

FIGURE 2 – WRITE MODE TIMING DIAGRAM



CIRCUIT SCHEMATIC



MC4304F,L, MC4305F,L, MC4004F,L,P, MC4005F,L,P (continued)

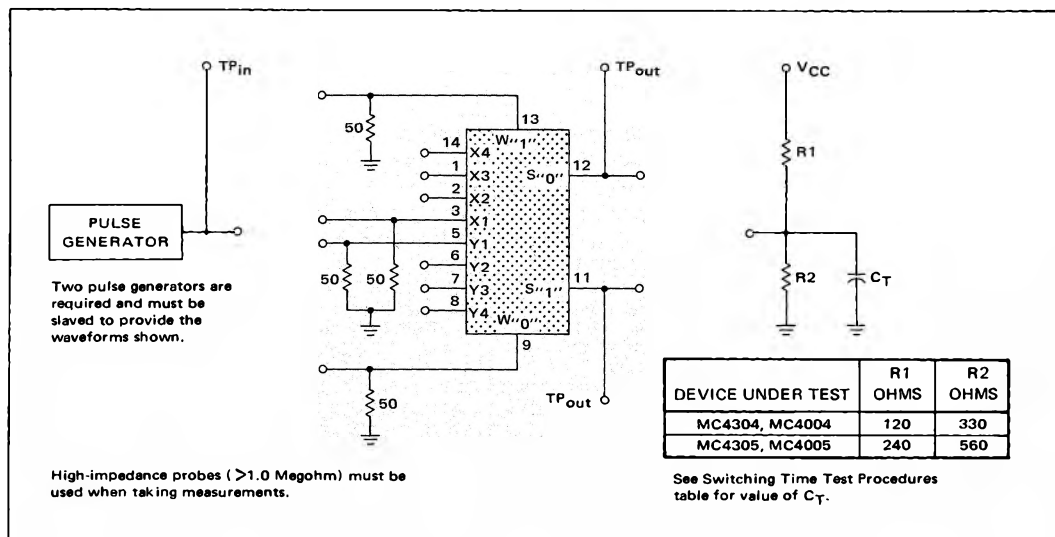
ELECTRICAL CHARACTERISTICS

Test procedures are shown for only one bit.
Other D/A are tested in the same manner.

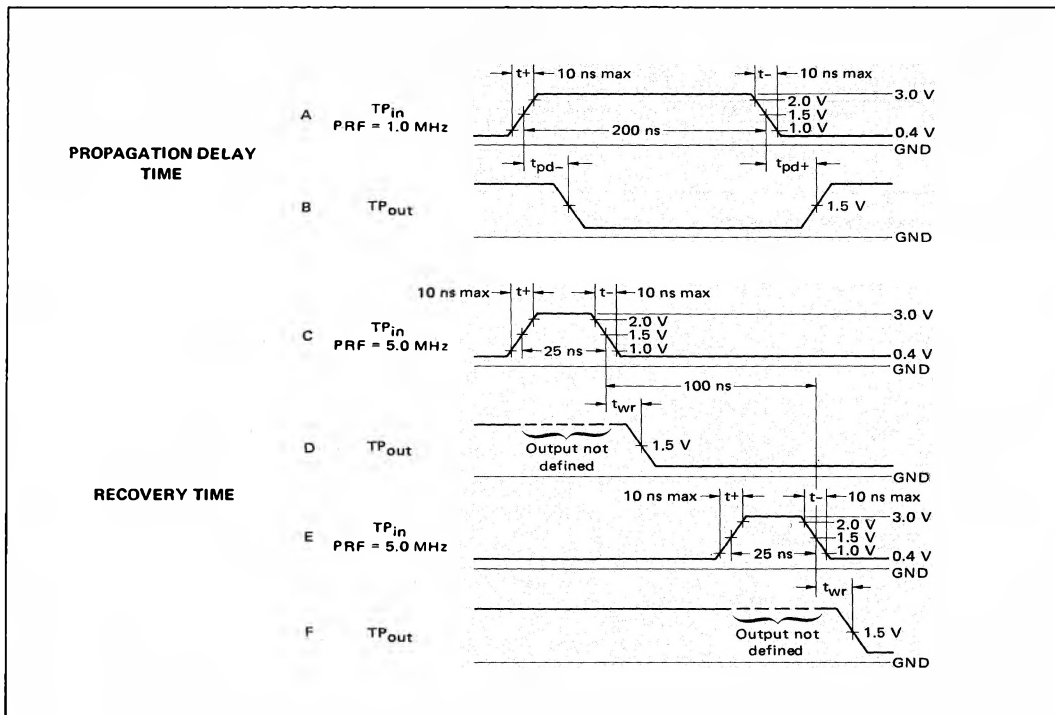
TEST CURRENT/VOLTAGE VALUES														
Characteristic	Symbol	Pin	MC4304, MC4305 Test Limits						TEST CURRENT/VOLTAGE APPLIED TO PINS LISTED BELOW:					
			-55°C			+25°C			0°C			+75°C		
			Min	Max	Typ	Min	Max	Typ	Min	Max	Typ	Min	Max	Typ
Input														
Forward Current														
Address Lines														
Write Inputs														
Leakage Current														
Address Lines														
Write Inputs														
Breakdown Voltage														
Address Lines														
Write Inputs														
Output														
Output Voltage														
Write "1"														
Logic "0" Level														
Logic "0" Inhibit														
Logic "0" Level														
Write "0"														
Logic "0" Level														
Logic "1" Inhibit														
Logic "0" Level														
Logic "1" Level														
Write "1"														
Logic "0" Level														
Leakage Current														
Write "1"														
Logic "0" Level														
Leakage Current														
Write "0"														
Leakage Current														
Write "1"														
Leakage Current														
Write "0"														
Leakage Current														
Power Requirements														
(Total Device)														
Power Supply Drain														
Current														

MC4304F,L, MC4305F,L, MC4004F,L,P, MC4005F,L,P (continued)

SWITCHING TIME TEST CIRCUIT



VOLTAGE WAVEFORMS AND DEFINITIONS



MC4304F,L, MC4305F,L, MC4004F,L,P, MC4005F,L,P (continued)

SWITCHING TIME TEST PROCEDURES (Letters shown in test columns refer to waveforms)

Test	Symbol	Pin Under Test	Input Pin											Output		C _T * pF	Limits	
			3 X ₁	2 X ₂	1 X ₃	14 X ₄	5 Y ₁	6 Y ₂	7 Y ₃	8 Y ₄	9 W ₀ "	13 W ₁ "	11 S ₀ "	12 S ₁ "	MC4304-5 ns max		MC4004-5 ns max	
Turn-Off Delay Time (Address Lines to Sense "0" Output)	**	—	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	3.0 V	—	—	—	—	—	
	**	—	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	—	—	—	—	—	
	t _{pd+}	11	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	B	—	30	23	23	
	t _{pd+}	11	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	B	—	200	35	35	
Turn-Off Delay Time (Address Lines to Sense "1" Output)	**	—	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	—	—	—	—	—	—	
	**	—	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	Gnd	Gnd	Gnd	3.0 V	—	—	—	—	—	
	t _{pd+}	12	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	—	B	30	23	23	
	t _{pd+}	12	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	—	B	200	35	35	
Turn-On Delay Time (Address Lines to Sense "0" Output)	**	—	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	3.0 V	—	—	—	—	—	
	**	—	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	—	—	—	—	—	
	t _{pd-}	11	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	B	—	30	23	23	
	t _{pd-}	11	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	B	—	200	35	35	
Turn-On Delay Time (Address Lines to Sense "1" Output)	**	—	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	—	—	—	—	—	—	
	**	—	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	Gnd	Gnd	Gnd	3.0 V	—	—	—	—	—	
	t _{pd-}	12	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	—	B	30	23	23	
	t _{pd-}	12	A	Gnd	Gnd	Gnd	A	Gnd	Gnd	Gnd	Gnd	Gnd	—	B	200	35	35	
Turn-Off Delay Time (4 Bits) (Address Lines to Sense "0" Output)	**	—	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	3.0 V	—	—	—	—	—	
	**	—	3.0 V	Gnd	Gnd	Gnd	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	—	—	—	—	—	
	t _{pd+}	11	A	Gnd	Gnd	Gnd	A	A	A	A	Gnd	Gnd	B	—	30	35	35	
Turn-Off Delay Time (4 Bits) (Address Lines to Sense "1" Output)	**	—	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	—	—	—	—	—	—	
	**	—	3.0 V	Gnd	Gnd	Gnd	3.0 V	3.0 V	3.0 V	3.0 V	Gnd	3.0 V	—	—	—	—	—	
	t _{pd+}	12	A	Gnd	Gnd	Gnd	A	A	A	A	Gnd	Gnd	—	B	30	35	35	
Write Recovery Time	t _{wr}	12	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	Gnd	Gnd	E	C	—	D	30	40	40	
		11	3.0 V	Gnd	Gnd	Gnd	3.0 V	Gnd	Gnd	Gnd	E	C	F	—	30	40	40	
Write Pulse Width	t _{wp}	—	Tested during t _{wr} tests.													ns min	ns min	
																25	25	

*Capacitance value for load of the Switching Time Test Circuit

**Preconditioning procedures for subsequent test.